

60.0A 200V Schottky Barrier Diode

Product Character

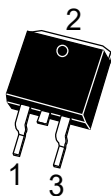
- Multilayer Metal -Silicon Potential Structure.
- Low Leakage Current.
- High Current Capability, High Efficiency.
- High Junction Temperature Capability.
- RoHs Product.

Primary Use

- Low Voltage High Frequency Switching Power Supply.
- Low Voltage High Frequency Invers Circuit.
- Low Voltage Continued Circuit and Protection Circuit.

Summarize

- MBR60200CD Device optimized for ultra-low forward voltage drop to maximize efficiency in Power Supply applications.

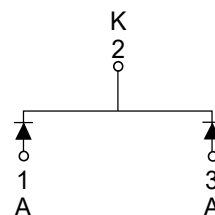


Package:TO-263-2L

MBR60200CD

MBR60200CD-HF

HF=Halogen Free



Absolute Maximum Ratings

Item	Symbol	Data	Unit
Maximal Inverted Repetitive Peak Voltage	V_{RRM}	200	V
Average Rectified Forward Current (Rated VR=20Khz Square Wave) - 50% duty cycle	I_{FAV}	60	A
Forward Peak Surge Current(Rated Load 8.3 Half Mssine Wave-According to JEDEC Method)	I_{FSM}	450×2	A
Operating Junction Temperature	T_J	-40~150	°C
Storage Temperature	T_{STG}	-40~150	°C
Typical Thermal Resistance(per leg)	Package=TO-263-2L $R_{\theta JC}$	2	°C/W

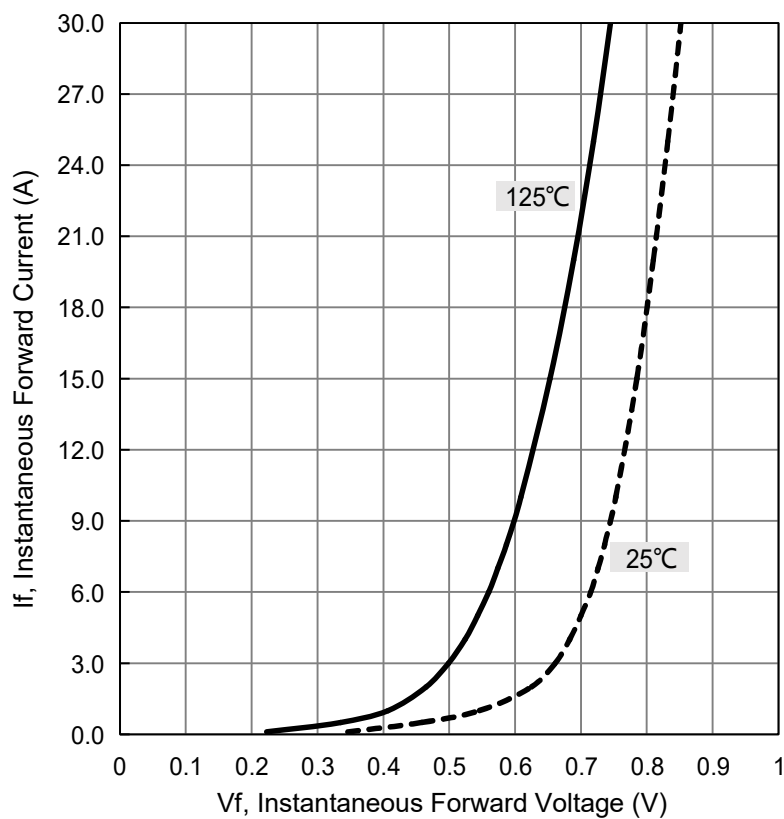
Electrical Characteristics

Item	Test Condition		Value(min)	Value(typ)	Value(max)	Unit
V_B	$T_J = 25^{\circ}C$	$I_R = 1mA$	200	---	---	V
I_R	$T_J = 25^{\circ}C$	$V_R = 200V$	---	---	0.02	mA
	$T_J = 125^{\circ}C$	$V_R = 200V$	---	---	10.00	mA
V_F	$T_J = 25^{\circ}C$	$I_F = 30A$	---	0.85	0.9	V
	$T_J = 125^{\circ}C$	$(I_{FAV} = 30A \times 2)$	---	---	0.85	V

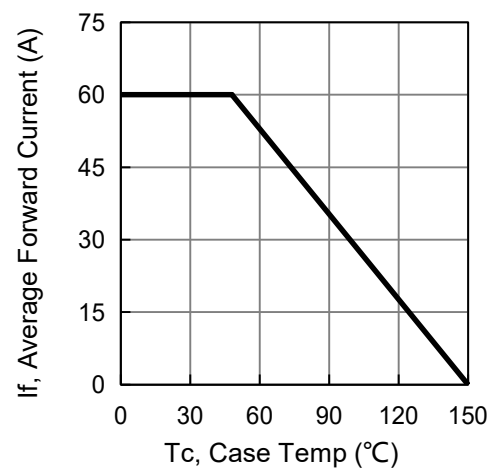


Characteristic Curves

The forward voltage and forward current curve



Current derating curve, per element



The reverse leak current and the reverse voltage (single-device) curve.

